length and a gate height, wherein a cross-sectional area of said gate electrode in a plane defined by said gate length and said gate height of the middle portion exceeds a value obtained by multiplying the gate length by the gate height.

Please add the following new claims 25-32:

25. (New) A transistor, comprising:

a substrate;

a gate insulation layer formed above said substrate; and

- a gate electrode formed above said gate insulation layer, said gate electrode having an upper portion and a lower portion, said upper portion having a plurality of extensions formed thereon, said extensions of said upper portion extending laterally beyond said lower portion of said gate electrode.
- 26. (New) The transistor of claim 25, further comprising an insulating material positioned adjacent said lower portion of said gate electrode and under said extensions formed on said upper portion.
  - 27. (New) The transistor of claim 25, wherein said substrate is comprised of silicon.
- 28. (New) The transistor of claim 25, wherein said gate insulation layer is comprised of silicon dioxide.